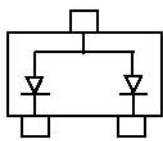
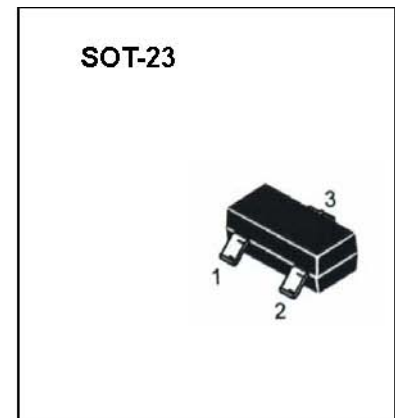


# BAW56/BAV70/BAV99

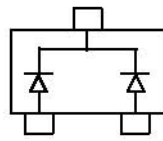
## BAW56/BAV70/BAV99 SWITCHING DIODE

### FEATURES

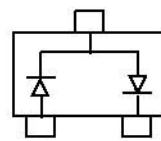
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56 Marking: A1



BAV70 Marking: A4



BAV99 Marking: A7

### Maximum Ratings @TA=25°C

Parameter	Symbol	Limits	Unit
Reverse voltage	$V_R$	70	V
Forward Current	$I_F$	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
Power Dissipation	$P_D$	225	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	556	°C/W
Junction temperature	$T_J$	150	°C
Storage temperature range	$T_{STG}$	-55-150	°C

### Electrical Characteristics @TA=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_R$	70			V	$I_R=100\mu A$
Forward voltage	$V_{F1}$			0.715	V	$I_F=1mA$
	$V_{F2}$			0.855	V	$I_F=10mA$
	$V_{F3}$			1	V	$I_F=50mA$
	$V_{F4}$			1.25	V	$I_F=150mA$
Reverse current	$I_R$			2.5	$\mu A$	$V_R=70V$
Capacitance between terminals	$C_T$			1.5	pF	$V_R=0, f=1MHz$
Reverse recovery time	$t_{rr}$			6	ns	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

## Typical Characteristics

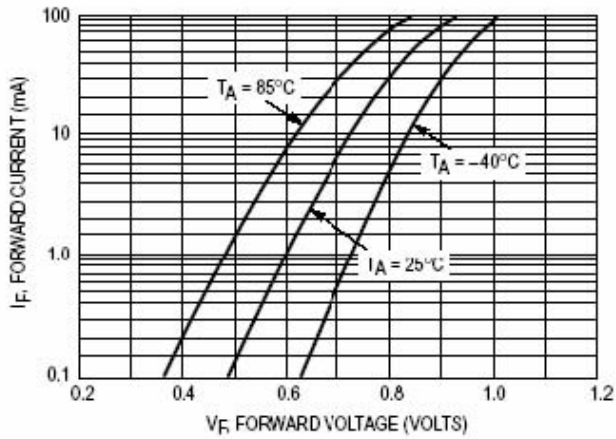


Figure 1. Forward Voltage

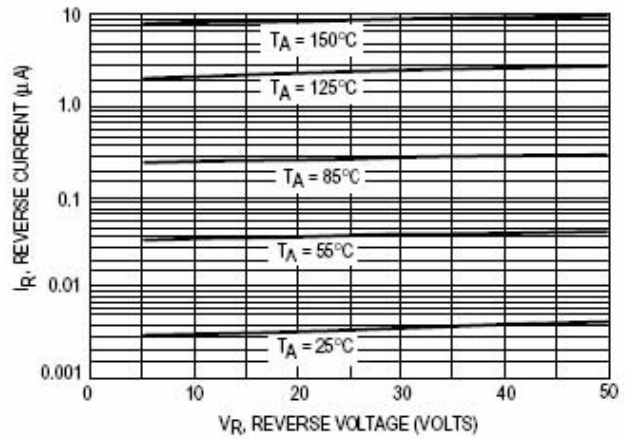


Figure 2. Leakage Current

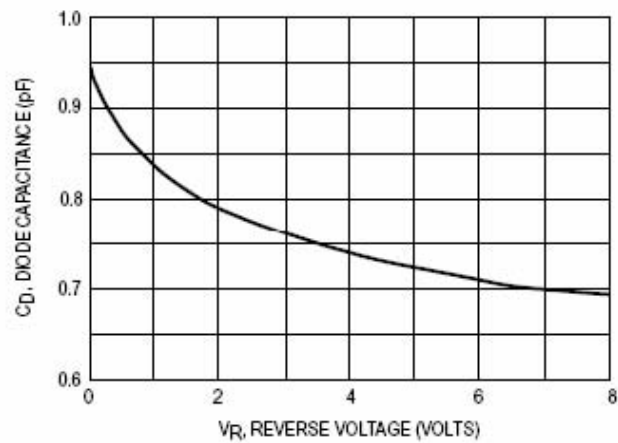


Figure 3. Capacitance

单击下面可查看定价，库存，交付和生命周期等信息

[>>YONGYUTAI\(永裕泰\)](#)